

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Robert DWILINSKI et al. Art Unit: 1791
U.S. Patent No. 7,387,677 Examiner: Malekzadeh, S.
Date of Patent: June 17, 2008 Application No.: 10/538,407
Filing Date : June 10, 2005
Title: SUBSTRATE FOR EPITAXY AND METHOD OF PREPARING THE SAME

ATTENTION: CERTIFICATE OF CORRECTIONS BRANCH

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

In reviewing the above-identified patent, a printing error was discovered therein requiring correction in order to conform to the Official Record in the application.

The error noted is set forth on the attached copy of Form PTO/SB/44 (09-07) in the manner required by the Commissioner's Notice.

Upon reviewing the patent it was noted that the fifth inventor's residence address list an incorrect address on the first page of the patent. Specifically, Mr. Yasuo Kanbara's residence address "Aman" should be --Anan--. It was also noted that the International Application Publication Number and the publication date list the incorrect publication number and publication date on the first page of the patent. Specifically, PCT Publication No. "WO02/101120" should be --WO2004/053210-- and PCT Publication Date "Dec. 19, 2002" should be --Jun. 24, 2004--.

REQUEST FOR CERTIFICATE OF CORRECTION
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Please see the enclosed a copy of the first page of the International Publication No. WO 2004/053210.

The \$100.00 fee for filing this Request is currently due. Please charge this fee to the Credit Card number listed on the EFS Registered Credit Card screen, referencing Attorney Docket No. 0047/028001. It is believed that this fee covers all of the required fees for filing this Request, however, if any additional fees are required, please charge these required fees to Deposit Account No. 19-2586, referencing Attorney Docket No. 0047/028001.

Accordingly, applicants respectfully request the USPTO to issue the Certificate of Correction for this patent.

If there are any questions regarding this application, please telephone the undersigned at the telephone number listed below.

Respectfully submitted,



Randolph A. Smith
Reg. No. 32,548

Date: August 12, 2008

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CERTIFICATE OF CORRECTION**Page 1 of 1

PATENT NO. : 7,387,677

APPLICATION NO.: 10/538,407

ISSUE DATE : June 17, 2008

INVENTOR(S) : Robert DWILINSKI et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On title page, Item (75) Inventors

"Yasuo Kanbara, Aman (JP)" should read -- Yasuo Kanbara, Anan (JP) --

Item (87) PCT Pub No.

"WO02/101120" should read -- WO2004/053210 --

Item (87) PCT Pub. Date

"Dec. 19, 2002" should read -- Jun. 24, 2004 --

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Smith Patent Office
1901 Pennsylvania Ave., N.W., Suite 901
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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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491-100, Oka, Kamimaka-cho, Anan-shi, Tokushima 774-8601 (JP).

(21) International Application Number:
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(72) Inventors; and

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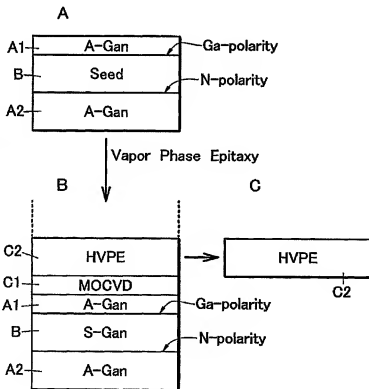
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(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR,

[Continued on next page]

(54) Title: A SUBSTRATE FOR EPI TAXY AND A METHOD OF PREPARING THE SAME



(57) Abstract: The substrate is used for opto-electric or electrical devices and comprises a layer of nitride grown by means of vapor phase epitaxy growth wherein both main surfaces of the nitride substrate are substantially consisting of non N-polar face and N-polar face respectively and the dislocation density of the substrate is 5 ~105/cm² or less. Therefore, the template type substrate has a good dislocation density and a good value of FWHM of the X-ray rocking curve from (0002) plane less than 80, so that the resulting template type substrate is very useful for the epitaxy substrate from gaseous phase such as MOCVD, MBE and HVPE, resulting in possibility of making good opto-electric devices such as Laser Diode and large-output LED and good electric devices such as MOSFET.